The following is a MARKED version of the amended pending claims and specification with all changes shown in conventional comparison.

IN THE SPECIFICATION:

Page 1:

Please replace the first paragraph on page 1 with the following paragraph:

[Description] FIELD OF THE INVENTION

The invention concerns a process as well as a device for in-situ decontamination of an EUV lithography device.

Please replace the second paragraph on Page 1 as follows:

BACKGROUND OF THE INVENTION

EUV lithography devices are used in the manufacturing of semiconductor components, e.g. integrated circuits. Lithography devices, which are operated in the wavelength range of extreme ultraviolet (e.g. at a wavelength of 13.4 nm), have primarily multi-layered systems of molybdenum and silicon, for example, as optical elements. EUV lithography devices display a vacuum or an inert gas atmosphere in their interior, however hydrocarbons and/or other carbon compounds cannot be completely prevented from appearing inside the device. These carbon compounds are split by the extreme ultraviolet radiation, leading to a film of contaminated carbons precipitating on the optical element. This contamination by carbon compounds leads to significant losses in reflectivity on the optical surface, which can have a considerable impact on the cost-efficiency of the EUV lithography process.

Page 4:

Please replace the first paragraph as follows:

SUMMARY OF THE INVENTION

Against this background, the task of the invention submitted is to provide a process, i.e. a device for decontaminating an EUV Lithography device, by which standstill periods are avoided and equipment changes to the EUV lithography device to be cleaned are kept to a minimum.

Page 9:

Please replace the first full paragraph as follows:

BRIEF DESCRIPTION OF THE DRAWINGS

The invention should be explained in more detail using a sample embodiment.

Please replace the third full paragraph as follows:

DETAILED DESCRIPTION OF THE INVENTION

The figure shows a schematic illustration of a sample embodiment, in which the dotted line indicates vacuum recipient 1 within the EUV lithography device, or in larger installations, vacuum recipient 1 in which the EUV lithography device as a whole is set up. Optical element 2 and the quartz crystal microwave 3 are set up within vacuum recipient 1. Optical element 2 involves reflectors with molybdenum-silicon, multi-layered systems for a wavelength of 13.4 nm. At this wavelength, the silicon-wafer is exposed by means of the lithography device.